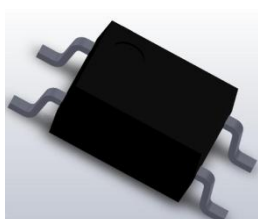




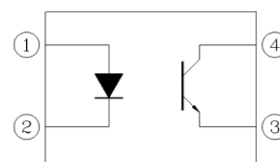
4 PIN SOP PHOTOTRANSISTOR PHOTOCOUPLER EL121N Series



Features:

- Halogens free
- Current transfer ratio
(CTR: 50~400% at $I_F = 5\text{mA}$, $V_{CE} = 5\text{V}$)
- High isolation voltage between input and output (Viso=3750 V rms)
- Compact 4 Pin SOP with a 2.0 mm profile
- Compliance with EU REACH.
- Pb free and RoHS compliant.
- UL and cUL approved(No. E214129)
- VDE approved (No. 132249)
- SEMKO approved
- NEMKO approved
- DEMKO approved
- FIMKO approved

Schematic



Pin Configuration

1. Anode
2. Cathode
3. Emitter
4. Collector

Description

The EL121N series contains an infrared emitting diode, optically coupled to a phototransistor detector. The devices in a 4-pin small outline SMD package.

Applications

- DC-DC Converters
- Programmable controllers
- Telecommunication equipments
- Signal transmission between circuits of different potentials and impedances

Absolute Maximum Ratings (T_a=25°C)

	Parameter	Symbol	Rating	Unit
Input	Forward current	I _F	50	mA
	Peak forward current (1us, pulse)	I _{FP}	1	A
	Reverse voltage	V _R	6	V
	Power dissipation	P _D	70	mW
	Derating factor (about T _a =100°C)		2.9	mW/°C
Output	Power dissipation	P _C	150	mW
	Derating factor (above T _a = 70°C)		3.7	mW/°C
	Collector current	I _C	50	mA
	Collector-Emitter voltage	V _{CEO}	80	V
	Emitter-Collector voltage	V _{ECO}	7	V
Total Power Dissipation		P _{TOT}	200	mW
Isolation Voltage ^{*1}		V _{ISO}	3750	V rms
Operating temperature		T _{OPR}	-55 ~ +110	°C
Storage temperature		T _{STG}	-55 ~ +125	°C
Soldering Temperature ^{*2}		T _{SOL}	260	°C

Notes:

*1 AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1, 2 are shorted together, and pins 3, 4 are shorted together.

*2 For 10 seconds

Electro-Optical Characteristics (T_a=25°C unless specified otherwise)

Input

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward voltage	V _F	-	1.2	1.4	V	I _F = 20mA
Reverse current	I _R	-	-	10	μA	V _R = 4V
Input capacitance	C _{in}	-	30	250	pF	V = 0, f = 1kHz

Output

Parameter	Symbol	Min	Typ.	Max.	Unit	Condition
Collector-Emitter dark current	I _{CEO}	-	-	100	nA	V _{CE} = 20V, I _F = 0mA
Collector-Emitter breakdown voltage	BV _{CEO}	80	-	-	V	I _C = 0.1mA
Emitter-Collector breakdown voltage	BV _{ECO}	7	-	-	V	I _E = 0.01mA

Transfer Characteristics (T_a=25°C unless specified otherwise)

Parameter	Symbol	Min	Typ.	Max.	Unit	Condition
Current Transfer ratio	EL121N	50	-	400	%	I _F = 5mA, V _{CE} = 5V
	EL121N B	130	-	260		
	EL121N C	200	-	400		
	EL121N BC	130	-	400		
Collector-Emitter saturation voltage	V _{CE(sat)}	-	0.1	0.2	V	I _F = 20mA, I _C = 1mA
Isolation resistance	R _{IO}	5×10 ¹⁰	-	-	Ω	V _{IO} = 500Vdc, 40~60% R.H.
Floating capacitance	C _{IO}	-	0.6	1.0	pF	V _{IO} = 0, f = 1MHz
Rise time	t _r	-	6	18	μs	V _{CE} = 2V, I _C = 2mA, R _L = 100Ω
Fall time	t _f	-	8	18		

* Typical values at T_a = 25°C

Typical Electro-Optical Characteristics Curves

Figure 1. Forward Current vs Forward Voltage

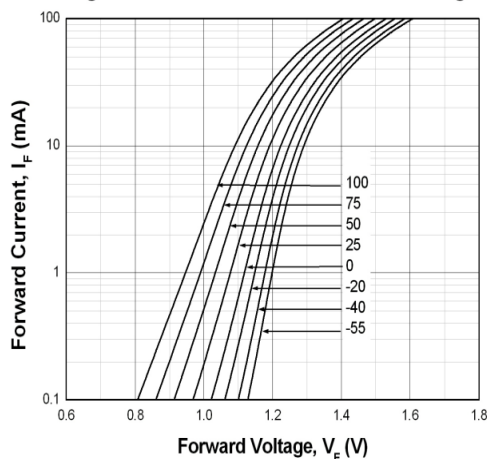


Figure 2. Normalized Collector Current vs Forward Current

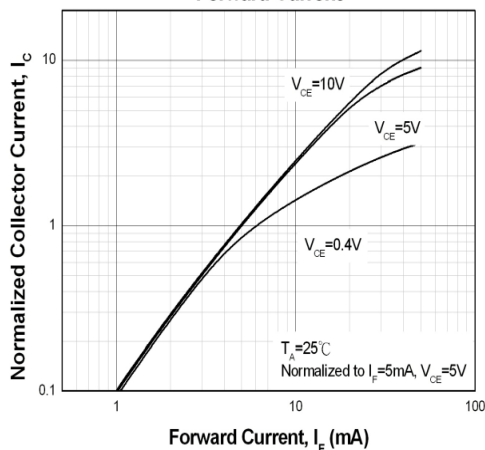


Figure 3. Normalized Current Transfer Ratio vs Forward Current

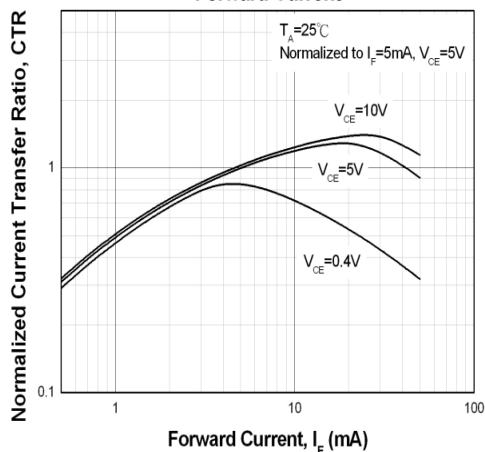


Figure 4. Normalized Collector Current vs Ambient Temperature

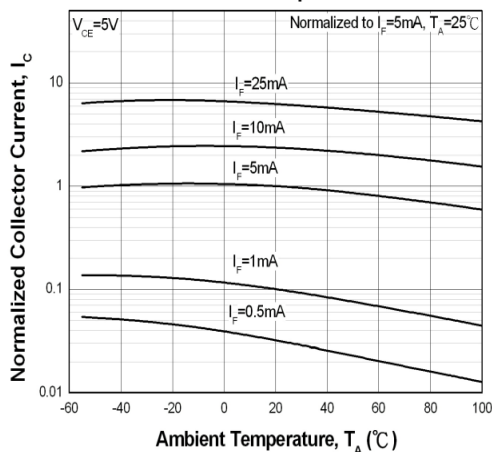


Figure 5. Collector Current vs Collector-Emitter Voltage

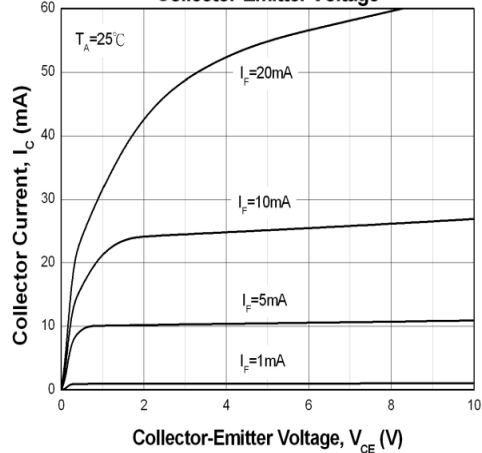


Figure 6. Collector Current vs Collector-Emitter Voltage

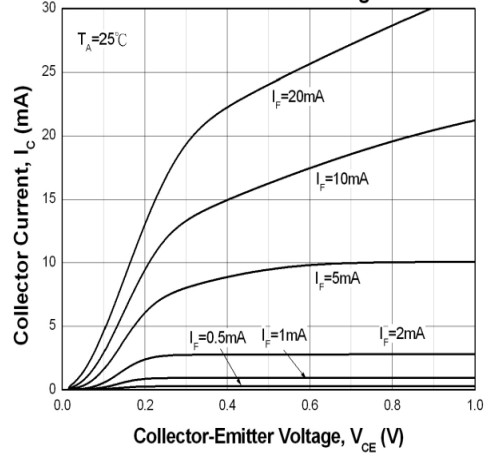


Figure 7. Collector Dark Current vs Ambient Temperature

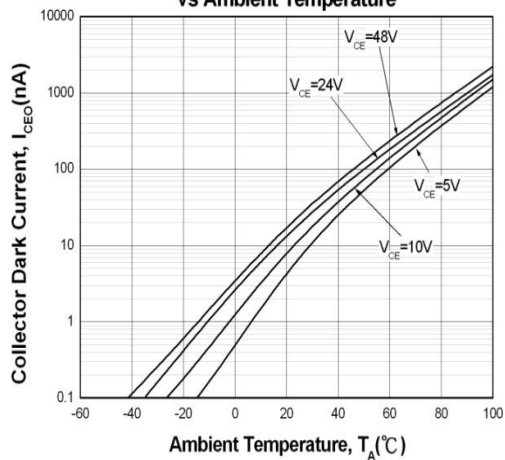


Figure 8. Switching Time vs Load Resistance

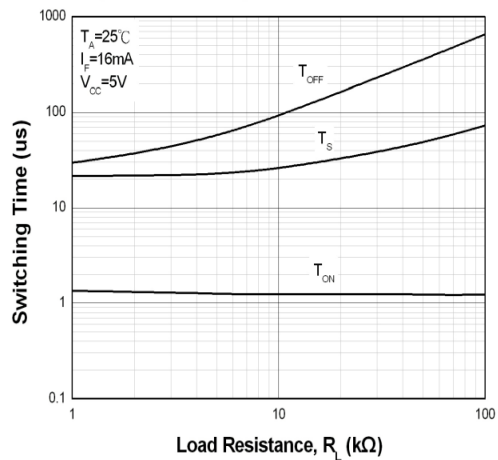


Figure 9. Collector-Emitter Saturation Voltage vs Ambient Temperature

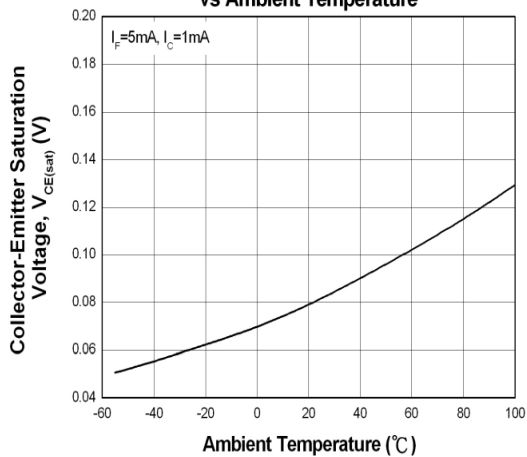
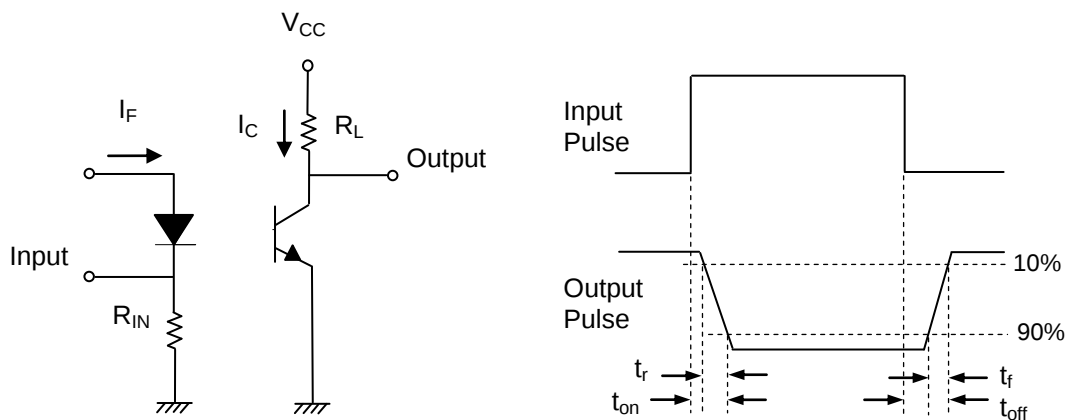


Figure 10. Switching Time Test Circuit & Waveforms



Order Information

Part Number

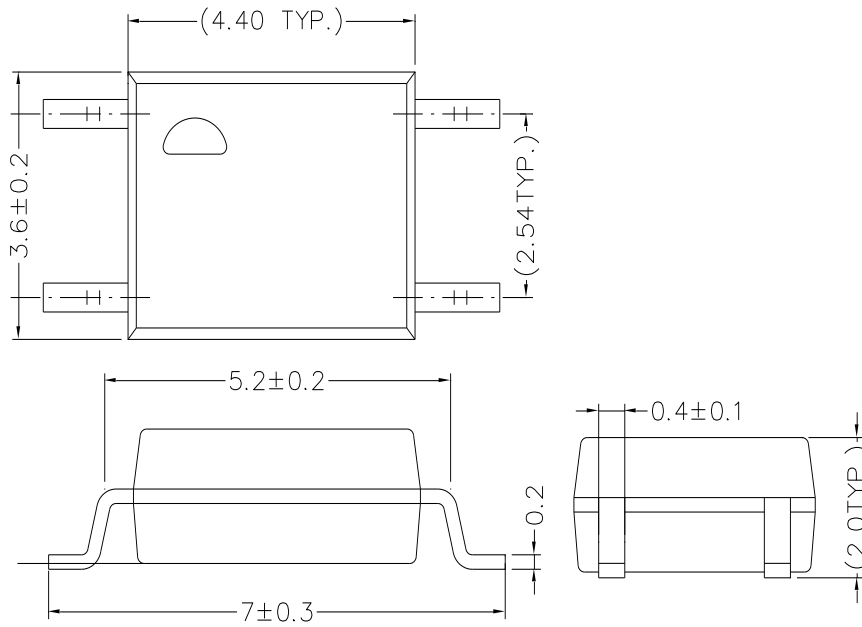
EL121N(X)(Y)-V

Note

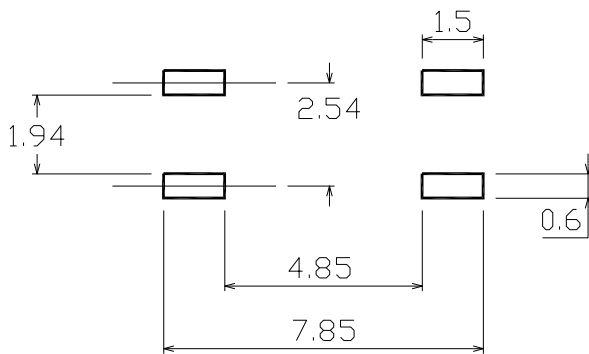
X = CTR Rank (B, C, BC or none)
Y = Tape and reel option (TA or TB).
V = VDE

Option	Description	Packing quantity
(TA)	TA Tape & reel option	3000 units per reel
(TB)	TB Tape & reel option	3000 units per reel
(TA)-V	TA Tape & reel option + VDE	3000 units per reel
(TB)-V	TB Tape & reel option + VDE	3000 units per reel

Package Dimension (Dimensions in mm)



Recommended pad layout for surface mount leadform



Device Marking



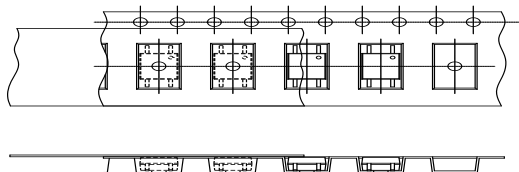
Notes

EL	denotes XI BNANG
121N	denotes Device Number
R	denotes CTR Rank (B or C)
Y	denotes 1 digit Year code
WW	denotes 2 digit Week code
V	denotes VDE



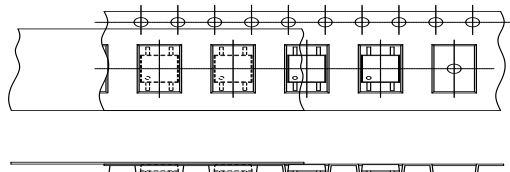
Tape & Reel Packing Specifications

Option TA



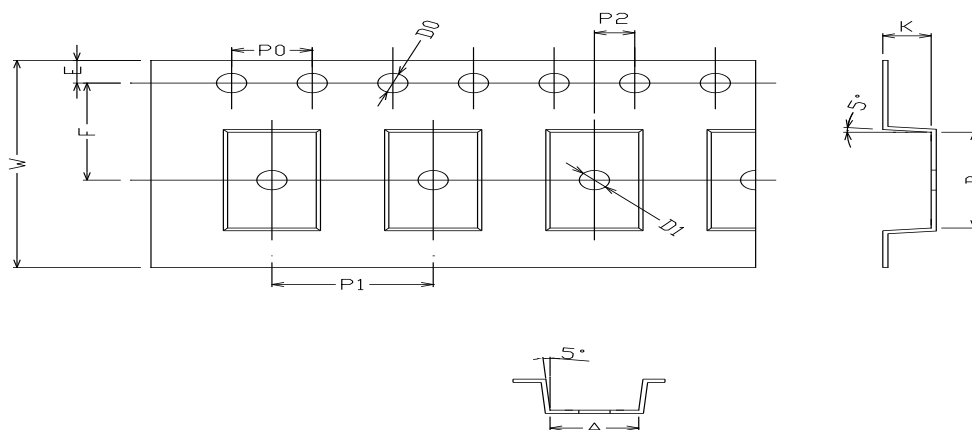
Direction of feed from reel

Option TB



Direction of feed from reel

Tape dimensions

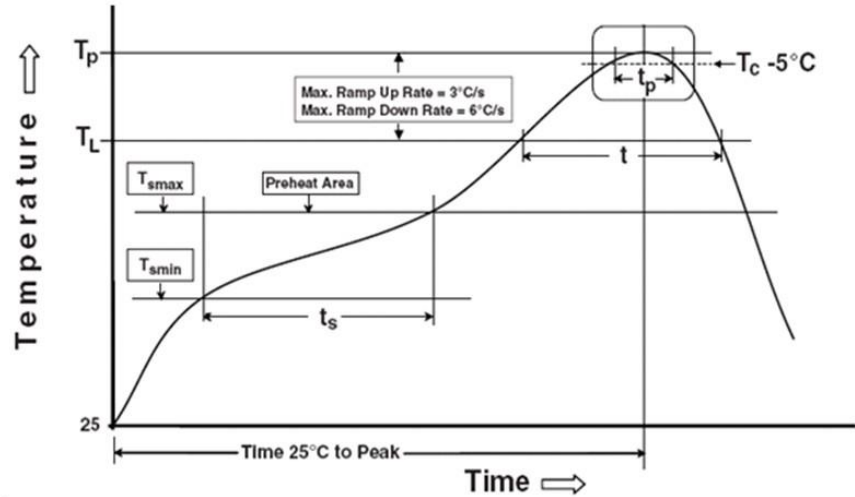


Tape dimensions

Dimension No.	A	B	Do	D1	E	F
Dimension (mm)	4.1 ± 0.1	7.6 ± 0.1	$1.5 + 0.1/-0$	1.5 ± 0.1	1.75 ± 0.1	7.5 ± 0.05
Dimension No.	Po	P1	P2	t	W	K
Dimension (mm)	4.0 ± 0.05	8.0 ± 0.1	2.0 ± 0.05	0.25 ± 0.05	16.0 ± 0.2	2.4 ± 0.1

Precautions for Use

- 1. Soldering Condition
 - 1.1 (A) Maximum Body Case Temperature Profile for evaluation of Reflow Profile



Note: Reference: IPC/JEDEC J-STD-020D

Preheat

Temperature min (T_{smin})	150 °C
Temperature max (T_{smax})	200°C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max

Other

Liquidus Temperature (T_L)	217 °C
Time above Liquidus Temperature (t_L)	60-100 sec
Peak Temperature (T_p)	260°C
Time within 5 °C of Actual Peak Temperature: $T_p - 5^\circ\text{C}$	30 s
Ramp- Down Rate from Peak Temperature	6°C /second max.
Time 25°C to peak temperature	8 minutes max.
Reflow times	3 times

DISCLAIMER

1. Above specification may be changed without notice. XI BNANG will reserve authority on material change for above specification.
2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. XI BNANG assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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